L Number	Hits	Search Text	DB	Time stamp
1	3499	(438/256,299,399,586,597,618,976).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 19:13
2	522	((438/256,299,399,586,597,618,976).CCLS.) and metalliz$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 19:14
8	54	(((438/256,299,399,586,597,618,976).CCLS.) and metalliz$5) and (arc (antireflect$4) (anti-reflect$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 19:41
9	18	((((438/256,299,399,586,597,618,976).CCLS.) and metalliz$5) and (arc (antireflect$4) (anti-reflect$4))) and (plasma adj etch$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 19:42
10	18	(((((438/256,299,399,586,597,618,976).CCLS.) and metalliz$5) and (arc (antireflect$4) (anti-reflect$4))) and (plasma adj etch$3)) and remov$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 19:42
12	207	((438/256,299,399,586,597,618,976).CCLS.) and (arc (antireflect$4) (anti-reflect$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 19:41
14	56	(((438/256,299,399,586,597,618,976).CCLS.) and (arc (antireflect$4) (anti-reflect$4))) and (plasma adj etch$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 19:42
15	55	((((438/256,299,399,586,597,618,976).CCLS.) and (arc (antireflect$4) (anti-reflect$4))) and (plasma adj etch$3)) and remov$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 19:45
16	2	(((((438/256,299,399,586,597,618,976).CCLS.) and (arc (antireflect$4) (anti-reflect$4))) and (plasma adj etch$3)) and remov$3) and (chf3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/10 19:46

Application No. **09/533,619**

MOSFET w/ ARC to plasma etch contact hole

East Search

3/1/02

Search	L No.	Hits	Text Search			Data Bases
IS&R	L1	3043	("438/256,299,399,586,597,618,976").CCLS.		3/1/02 15:45	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L2	445	1 and metalliz$5		3/1/02 15:47	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L3	23	2 and (anti-reflect$8 (anti adj reflect$8))		3/1/02 15:50	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L4	89	1 and (anti-reflect$8 (anti adj reflect$8))		3/1/02 15:49	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L5	182	1 and (sion sino sin)		3/1/02 15:49	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L6	26	5 and (anti-reflect$8 (anti adj reflect$8))		3/1/02 15:50	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L7	388	1 and plasma adj etch$4		3/1/02 15:50	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L8	23	7 and (anti-reflect$8 (anti adj reflect$8))		3/1/02 15:50	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB

Search Result

USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor
US 6326301 B1	20011204	14	Method for forming a dual inlaid copper interconnect structure	438/638	438/618 ; 438/634 ; 438/687 ; 438/970	Venkatesan, Suresh , et al.
US 6323121 B1	20011127	9	Fully dry post-via-etch cleaning method for a damascene process	438/633	156/345 ; 430/314 ; 430/329 ; 430/330 ; 438/597 ; 438/738	Liu, Jen-Cheng , et al.
US 6294457 B1	20010925	7	Optimized IMD scheme for using organic low-k material as IMD layer	438/623	438/597 ; 438/631 ; 438/759 ; 438/763	Liu, Chung-Shi
US 6271115 B1	20010807	11	Post metal etch photoresist strip method	438/618	430/330 ; 438/710 ; 438/725	Liu, Wen Jun , et al.
US 6090697 A	20000718	20	Etchstop for integrated circuits	438/618	438/643	Xing, Guoqiang , et al.
US 5946589 A	19990831	8	Elimination of void formation in aluminum based interconnect structures	438/586	438/595 ; 438/688	Ng, Yat Meng , et al.

Application No. **09/533,619**

MOSFET w/ ARC to plasma etch contact hole

East Search 3/1/02

Search	L No.	Hits	Text Search			Data Bases
IS&R	L1	3270	("257/244,245,249,382,503,508,621,622,632").CCLS.		3/1/02 14:41	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L2	405	1 and contact adj hole		3/1/02 15:13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L5	30	4 and ((contact adj hole) opening groove trench)		3/1/02 15:02	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L6	8	5 and plasma adj etch$3		3/1/02 15:03	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
IS&R	L12	3263	("438/396").CCLS.		3/1/02 15:11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L13	30	12 and (arc (antireflective adj coat$4))		3/1/02 15:12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L14	9	13 and plasma adj etch$3		3/1/02 15:12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L15	8	14 and ((contact adj hole) opening groove trench)		3/1/02 15:13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB

Search Result

USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor
US 20010017416 A1		16	Device having metal interconnects with reduced or eliminated metal recess in vias			Sengupta, Samit , Zheng, Tammy
US 6300672 B1	20011009	9	Silicon oxynitride cap for fluorinated silicate glass film in intermetal dielectric semiconductor fabrication	257/641	257/632 ; 257/639 ; 438/624	Lee, Gill Yong
US 5710067 A	19980120	13	Silicon oxime film	438/636	257/632 ; 257/649 ; 423/325 ; 427/574 ; 427/579 ; 438/740 ; 438/786	Foote, David K. , et al.